

U.S.S.N. 10/077,720

Specification Amendments

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Please replace the paragraph beginning on page 14, paragraph 0028 with the following rewritten paragraph:

0027 Figures 1A through 1C show a series of steps performed to complete an etching process in a semiconductor structure, for example, a via or contact hole. In Figures 1A through 1C is depicted a photoresist layer 12 overlying a DARC layer 10, followed by a low-k material 14 and finally an etching stop layer 16. In Figures 1A through 1C is represented the etching of, for example, a via hole 20 where the low-k material 14 is for example, an inter-metal dielectric (IMD). As shown in Figure 1A, an etching process with a chemistry that is capable of selectively etching an inorganic dielectric anti-reflective coating (DARC) layer is required in the first step. The DARC is preferably a nitride containing material and more preferably, at least one of silicon nitride, silicon oxynitride, and titanium nitride. The DARC may also be a low-k carbon containing dielectric material layer.